Schottky Barrier Diodes, Dual Common Cathode

BAT54CL

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand-held and portable applications where space is limited.

Features

- Extremely Fast Switching Speed
- Low Forward Voltage 0.35 V (Typ) @ $I_F = 10 \text{ mAdc}$
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_{.I} = 125°C unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	30	V
Forward Power Dissipation @ T _A = 25°C Derate above 25°C	P _F	225 1.8	mW mW/°C
Thermal Resistance (Note 1) Junction-to-Ambient (Note 2)	$R_{\theta JA}$	508 311	°C/W
Forward Current (DC)	I _F	200 Max	mA
Non-Repetitive Peak Forward Current t _p < 10 msec	I _{FSM}	600	mA
Repetitive Peak Forward Current Pulse Wave = 1 sec, Duty Cycle = 66%	I _{FRM}	300	mA
Junction Temperature	TJ	-55 to +150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 inch Pad.



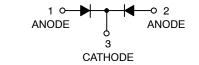
ON Semiconductor®

www.onsemi.com

30 VOLT DUAL COMMON CATHODE SCHOTTKY BARRIER DIODES



SOT-23 CASE 318 STYLE 9



MARKING DIAGRAM



5C = Device Code
M = Date Code
■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BAT54CLT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SBAT54CLT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BAT54CLT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

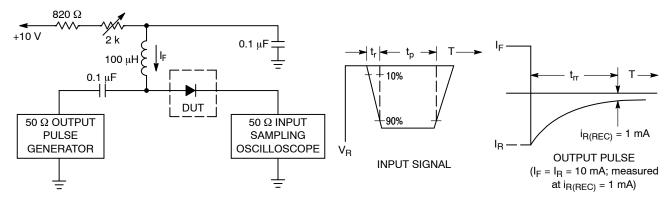
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BAT54CL

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μA)	V _{(BR)R}	30	-	-	V
Total Capacitance (V _R = 1.0 V, f = 1.0 MHz)	C _T	_	7.6	10	pF
Reverse Leakage (V _R = 25 V)	I _R	-	0.5	2.0	μА
Forward Voltage (I _F = 0.1 mA) (I _F = 1.0 mA) (I _F = 10 mA) (I _F = 30 mA) (I _F = 100 mA)	V _F	- - - -	0.22 0.29 0.35 0.41 0.52	0.24 0.32 0.40 0.50 0.80	V
Reverse Recovery Time (I _F = I _R = 10 mAdc, I _{R(REC)} = 1.0 mAdc, Figure 1)	t _{rr}	-	_	5.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (IF) of 10 mA.

- 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
- 3. t_p » t_{rr}

Figure 1. Recovery Time Equivalent Test Circuit

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TYPICAL CHARACTERISTICS

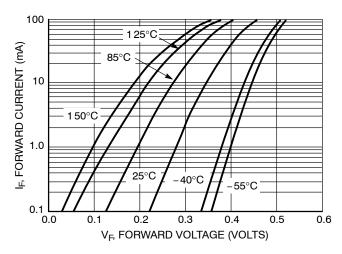


Figure 2. Forward Voltage

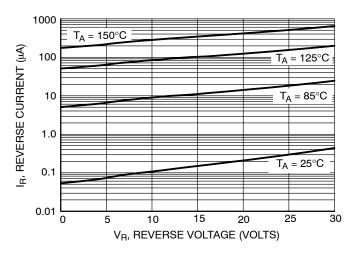


Figure 3. Leakage Current

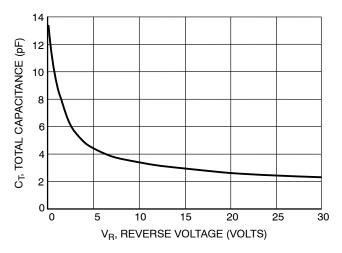


Figure 4. Total Capacitance

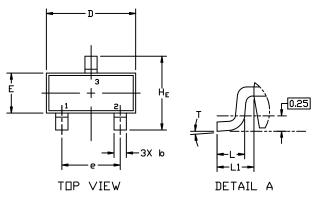




SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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